

Title (en)  
SEMICONDUCTOR ARRANGEMENT COMPRISING TRANSISTORS BASED ON ORGANIC SEMICONDUCTORS AND NON-VOLATILE READ-WRITE MEMORY CELLS

Title (de)  
HALBLEITERANORDNUNG MIT TRANSISTOREN AUF BASIS ORGANISCHER HALBLEITER UND NICHTFLÜCHTIGER SCHREIB-LESE-SPEICHERZELLEN

Title (fr)  
MONTAGE A SEMI-CONDUCTEURS AVEC TRANSISTORS A BASE DE SEMI-CONDUCTEURS ORGANIQUES ET DE CELLULES DE MEMOIRE D'ECRITURE-LECTURE NON VOLATILES

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Application  
**EP 02785070 A 20021115**

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Abstract (en)  
[origin: DE10156470A1] The invention relates to a semiconductor arrangement consisting of transistors, the semiconductor segment of said transistors consisting of an organic semiconductor, and memory cells based on a ferroelectric effect, preferably in a polymer, for using, for example, in RFID tags.  
[origin: DE10156470A1] Semiconductor arrangement comprises a semiconductor device having a semiconductor path made from an organic semiconductor and a rewritable storage cell based on the ferroelectric effect in a storage material. Preferably the storage material is an organic polymer having ferroelectric properties or an inorganic material having ferroelectric properties. The organic polymer is a fluorinated polyene, preferably a poly vinylidene fluoride. The inorganic material is a ferroelectric titanate or tantalate.

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